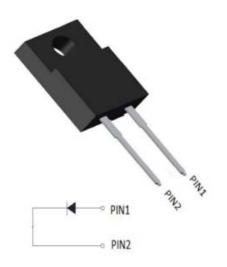






Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F (125°C)}	8A
Qc	30nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: ITO-220AC

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106508FQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	650
Continuous forward current @ T _c =25°C		_	16
Continuous forward current @ T _c =125°C	l _F	Α	8
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	70
Power Dissipation@ T _c =25°C	D W		43
Power Dissipation@ T₀=110°C	P _{TOT}	W	19
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	24
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

YJD106508FQG2

■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop V _F	V	V	I _F =8A, T _j =25°C	1.3	1.55
	V _F		I _F =8A, T _j =175°C	1.6	-
Poverse leakage current	I _R μA	V _R =650V, T _j =25°C	0.5	25	
Reverse leakage current		μΑ	V _R =650V, T _j =175°C	2	-
Total capacitive charge	Qc	nC	V_R =400V, T_j =25°C , QC = $\int_0^{VR}C(V)dV$	30	-
			V _R =0V, f=1MHZ	543	-
Total capacitance	С	pF	V _R =200V, f=1MHZ	55	-
			V _R =400V, f=1MHZ	52	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	3.7	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C W	3.5

■Typical Characteristics

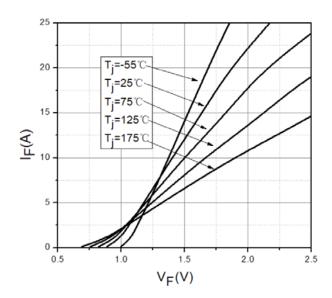
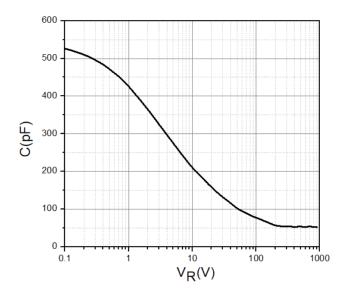


Figure 1. Forward Characteristics

Figure2. Reverse Characteristic



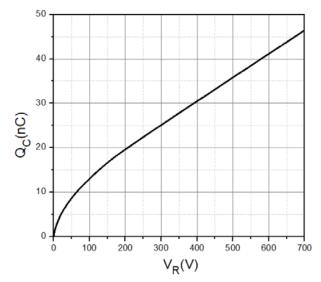
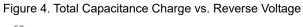
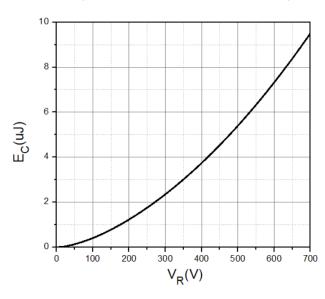
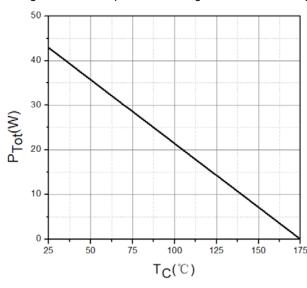


Figure 3. Capacitance vs. Reverse Voltage







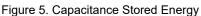
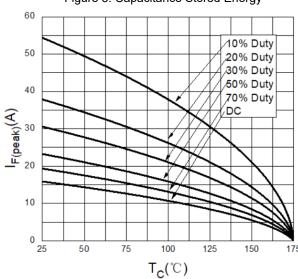


Figure 6. Power Derating



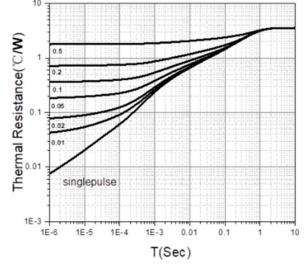
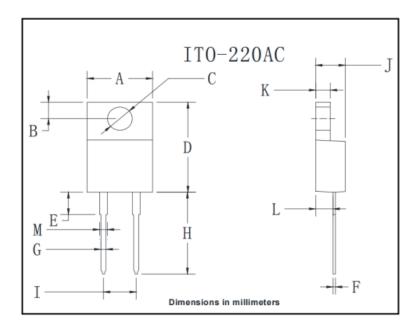


Figure 7. Current Derating

Figure 8. Transient Thermal Impedance



■Outline Dimensions



ITO-220AC			
Dim	Min	Max	
Α	9.8	10.2	
В	2.25	2.75	
С	2.95	3.45	
D	14.75	15.25	
E	3.5	4.1	
F	0.45	0.75	
G	0.45	0.75	
Н	13.35	14.15	
I	4.97	5.23	
J	4.3	4.8	
K	2.5	2.74	
L	2.58	2.82	
M	1.03	1.43	



YJD106508FQG2

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http:// www.frxelec.com, or consult your nearest Yangjie's sales office for further assistance.